

MOSFETs Silicon N-Channel MOS (DTMOSVI)

TK200V65Z5

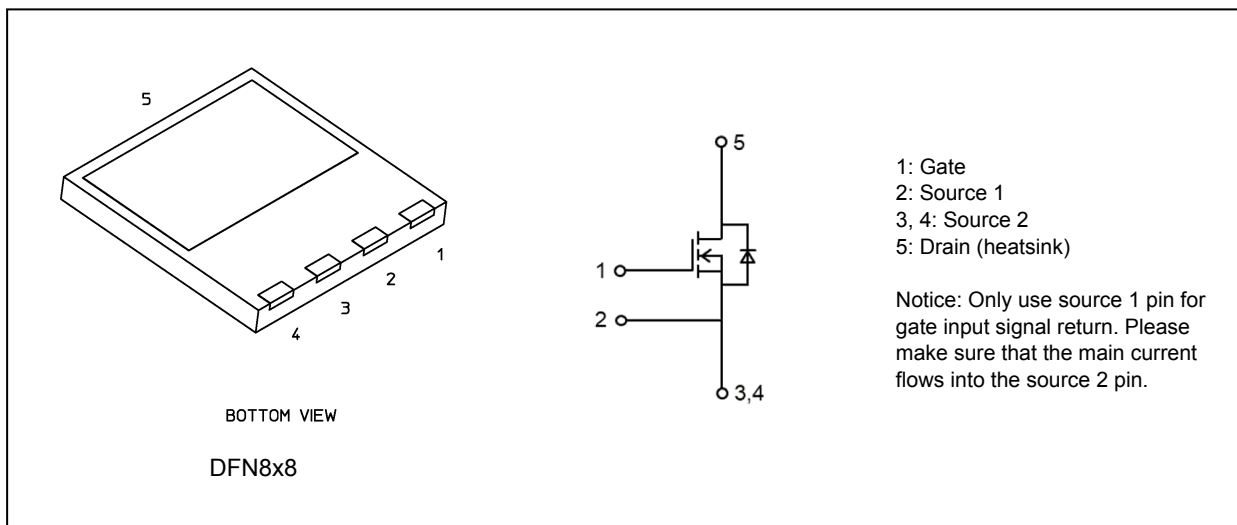
1. Applications

- Switching Voltage Regulators

2. Features

- (1) Fast reverse recovery time: $t_{rr} = 95$ ns (typ.)
- (2) Low drain-source on-resistance: $R_{DS(ON)} = 0.154$ Ω (typ.)
- (3) High-speed switching properties with lower capacitance.
- (4) Enhancement mode: $V_{th} = 3.5$ to 4.5 V ($V_{DS} = 10$ V, $I_D = 0.61$ mA)

3. Packaging and Internal Circuit



Start of commercial production
2024-11

4. Absolute Maximum Ratings (Note) ($T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	650	V
Gate-source voltage	V_{GSS}	± 30	
Drain current (DC) (Note 1)	I_D	15	A
Drain current (pulsed) (Note 1)	I_{DP}	60	
Power dissipation ($T_c = 25\text{ }^\circ\text{C}$)	P_D	130	W
Single-pulse avalanche energy (Note 2)	E_{AS}	204	mJ
Single-pulse avalanche current	I_{AS}	3	A
Reverse drain current (DC) (Note 1)	I_{DR}	15	
Reverse drain current (pulsed) (Note 1)	I_{DRP}	60	
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	$R_{th(ch-c)}$	0.961	$^\circ\text{C/W}$

Note 1: Ensure that the channel temperature does not exceed $150\text{ }^\circ\text{C}$.

Note 2: $V_{DD} = 90\text{ V}$, $T_{ch} = 25\text{ }^\circ\text{C}$ (initial), $L = 40.2\text{ mH}$, $I_{AS} = 3\text{ A}$

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics ($T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	$V_{GS} = \pm 30\text{ V}$, $V_{DS} = 0\text{ V}$	—	—	± 1	μA
Drain cut-off current	I_{DSS}	$V_{DS} = 650\text{ V}$, $V_{GS} = 0\text{ V}$	—	—	100	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 10\text{ mA}$, $V_{GS} = 0\text{ V}$	650	—	—	V
Gate threshold voltage	V_{th}	$V_{DS} = 10\text{ V}$, $I_D = 0.61\text{ mA}$	3.5	—	4.5	
Drain-source on-resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{ V}$, $I_D = 7.5\text{ A}$	—	0.154	0.200	Ω

6.2. Dynamic Characteristics ($T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	C_{iss}	$V_{DS} = 300\text{ V}, V_{GS} = 0\text{ V}, f = 100\text{ kHz}$	—	1400	—	pF
Reverse transfer capacitance	C_{rss}		—	1.2	—	
Output capacitance	C_{oss}		—	38	—	
Effective output capacitance (energy related) (Note 3)	$C_{o(er)}$	$V_{DS} = 0\text{ to }400\text{ V}, V_{GS} = 0\text{ V}$	—	58	—	
Effective output capacitance (time related) (Note 4)	$C_{o(tr)}$		—	375	—	
Gate resistance	r_g	$V_{DS} = \text{OPEN}, f = 1\text{ MHz}$	—	2.8	—	Ω
Switching time (rise time)	t_r	See Fig. 6.2.1	—	10	—	ns
Switching time (turn-on time)	t_{on}		—	35	—	
Switching time (fall time)	t_f		—	4.4	—	
Switching time (turn-off time)	t_{off}		—	60	—	
MOSFET dv/dt ruggedness	dv/dt	$V_{DS} \leq V_{DSS}, I_D \leq 7.5\text{ A}$	90	—	—	V/ns

Note 3: $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 V to 400 V.

Note 4: $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 V to 400 V.

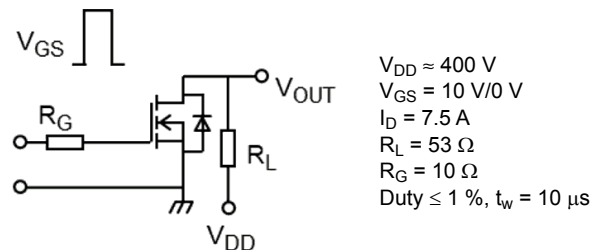


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	$V_{DD} \approx 400\text{ V}, V_{GS} = 10\text{ V}, I_D = 15\text{ A}$	—	26	—	nC
Gate-source charge 1	Q_{gs1}		—	8.8	—	
Gate-drain charge	Q_{gd}		—	8.8	—	

6.4. Source-Drain Characteristics ($T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Diode forward voltage	V_{DSF}	$I_{DR} = 15\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.7	V
Reverse recovery time (Note 5)	t_{rr}	$V_{DD} = 400\text{ V}, I_{DR} = 7.5\text{ A}, V_{GS} = 0\text{ V}, -di_{DR}/dt = 100\text{ A}/\mu\text{s}$	—	95	152	ns
Reverse recovery charge	Q_{rr}		—	0.4	—	μC
Peak reverse recovery current	I_{rr}		—	8.4	—	A
Diode dv/dt ruggedness	dv/dt	$V_{DD} \leq 400\text{ V}, I_{DR} \leq 7.5\text{ A}, V_{GS} = 0\text{ V}$	70	—	—	V/ns

Note 5: Defined by design.

7. Marking (Note)

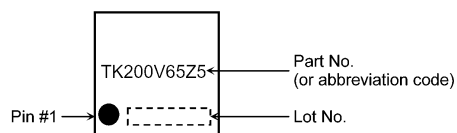


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

8. Characteristics Curves (Note)

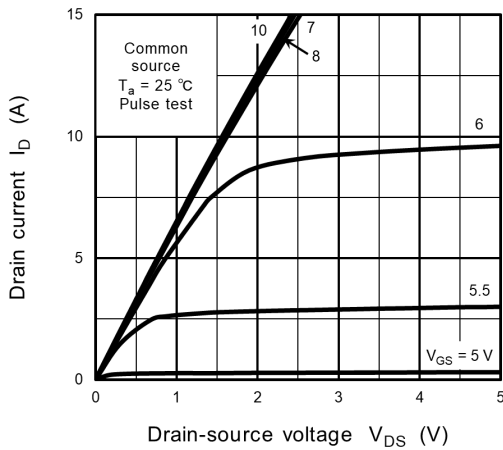


Fig. 8.1 $I_D - V_{DS}$

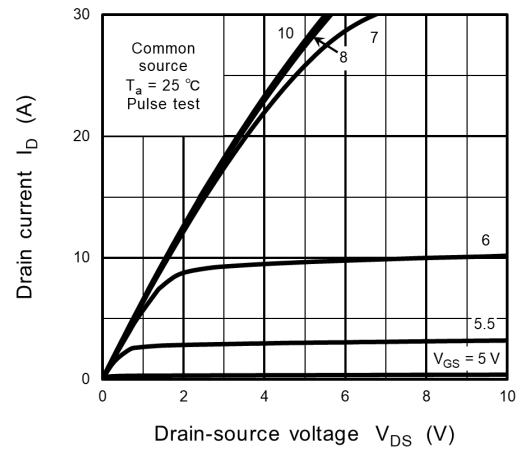


Fig. 8.2 $I_D - V_{DS}$

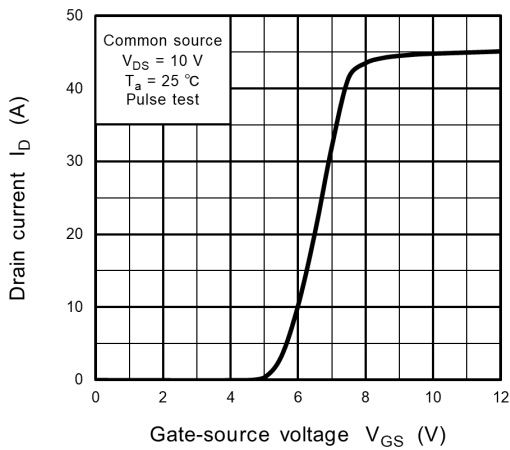


Fig. 8.3 $I_D - V_{GS}$

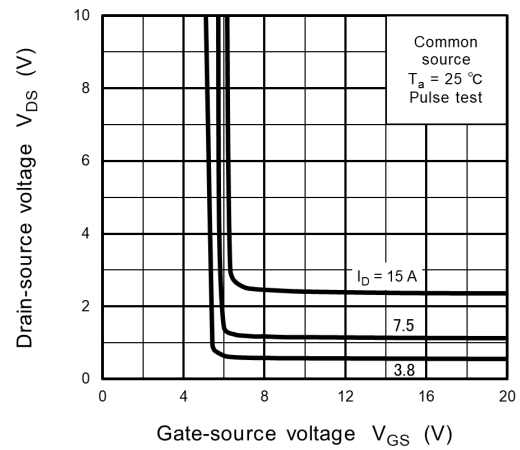


Fig. 8.4 $V_{DS} - V_{GS}$

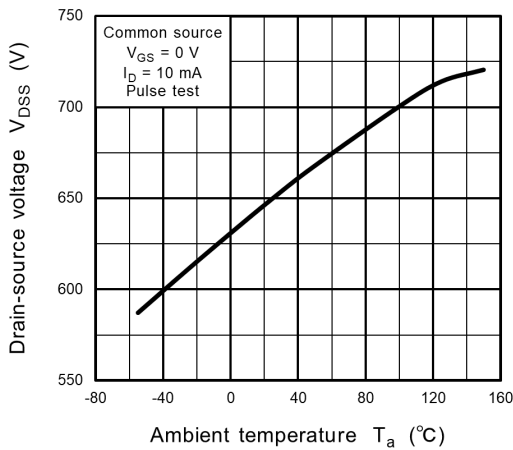


Fig. 8.5 $V_{DSS} - T_a$

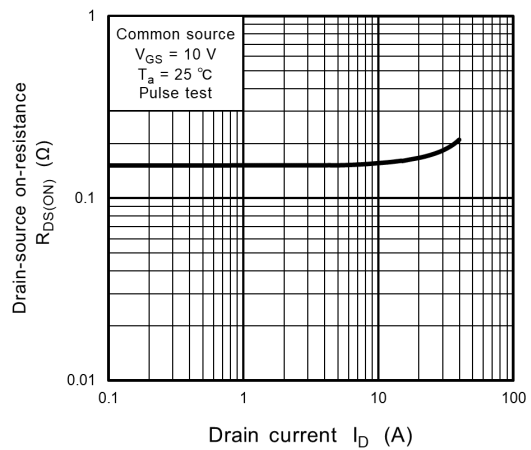


Fig. 8.6 $R_{DS(ON)} - I_D$

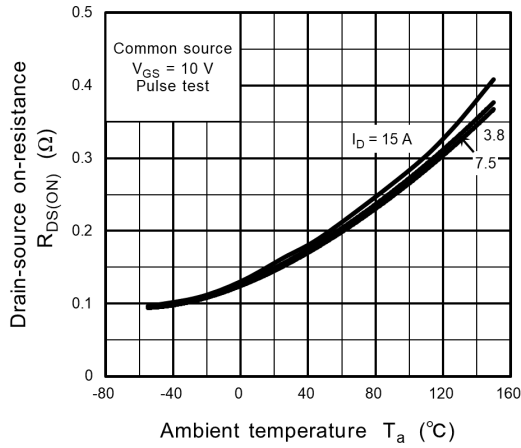


Fig. 8.7 $R_{DS(ON)} - T_a$

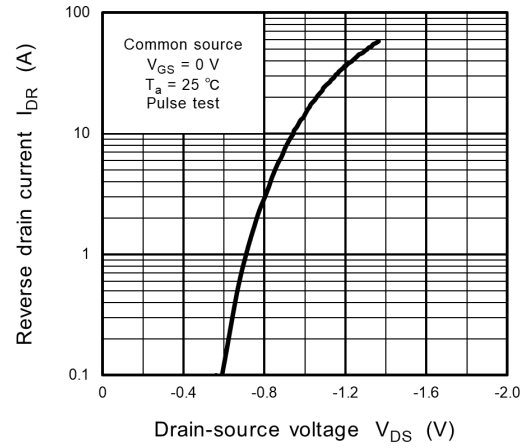


Fig. 8.8 $I_{DR} - V_{DS}$

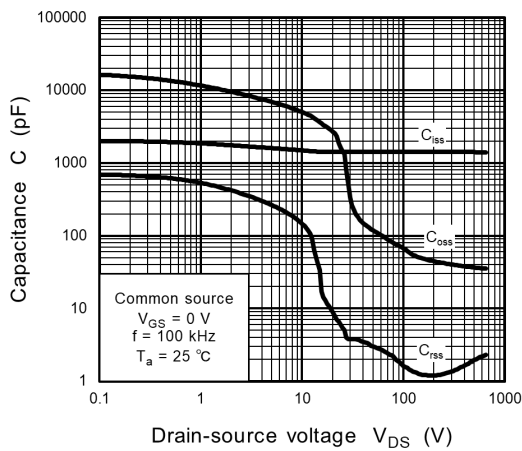


Fig. 8.9 $C - V_{DS}$

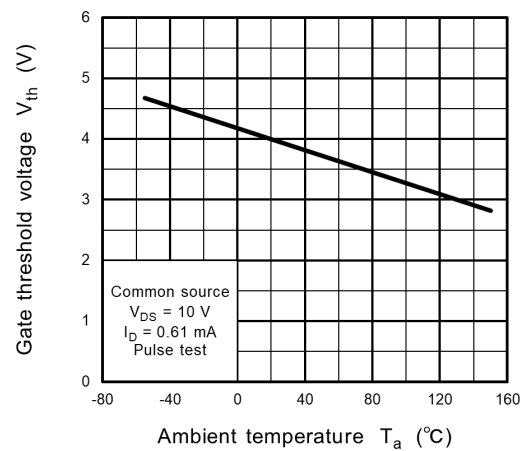


Fig. 8.10 $V_{th} - T_a$

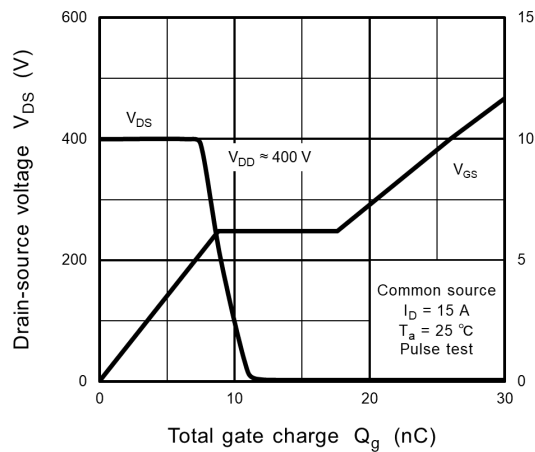


Fig. 8.11 Dynamic Input/Output Characteristics

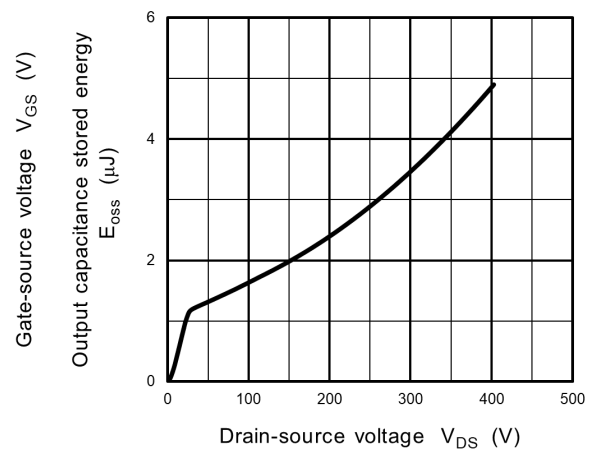


Fig. 8.12 $E_{oss} - V_{DS}$

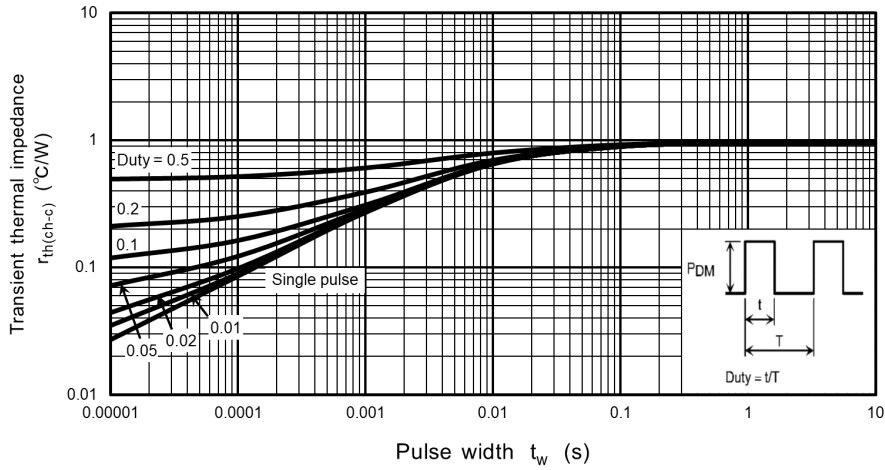


Fig. 8.13 $r_{th} - t_w$
(Guaranteed Maximum)

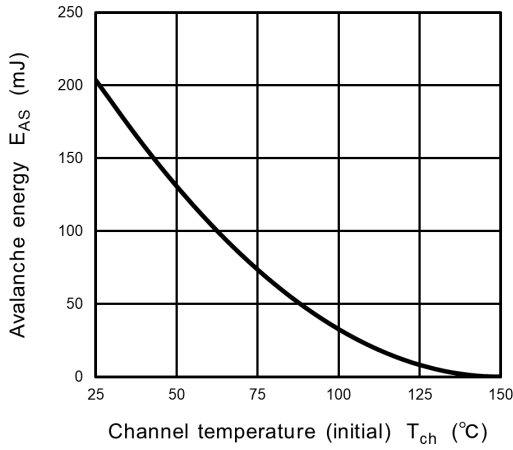


Fig. 8.14 $E_{AS} - T_{ch}$
(Guaranteed Maximum)

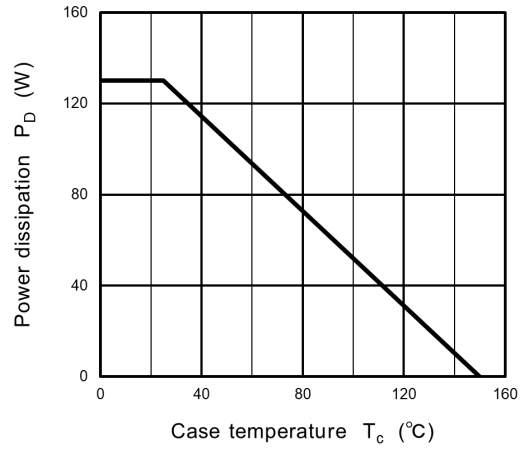


Fig. 8.15 $P_D - T_c$
(Guaranteed Maximum)

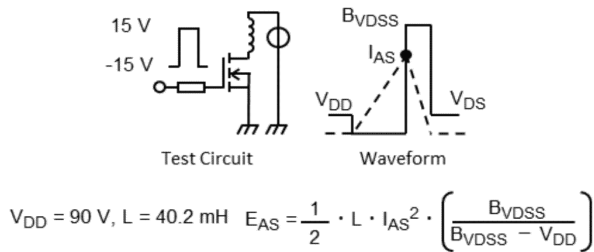


Fig. 8.16 Test Circuit/Waveform

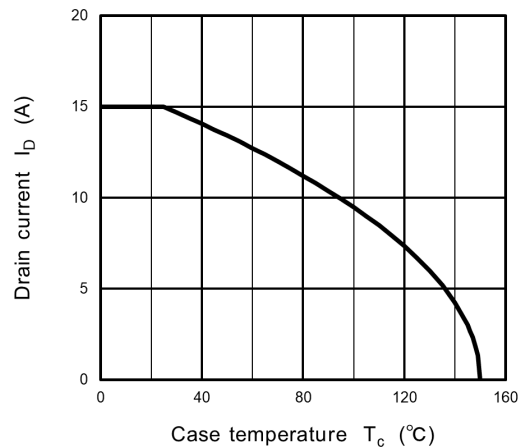


Fig. 8.17 $I_D - T_c$
(Guaranteed Maximum)

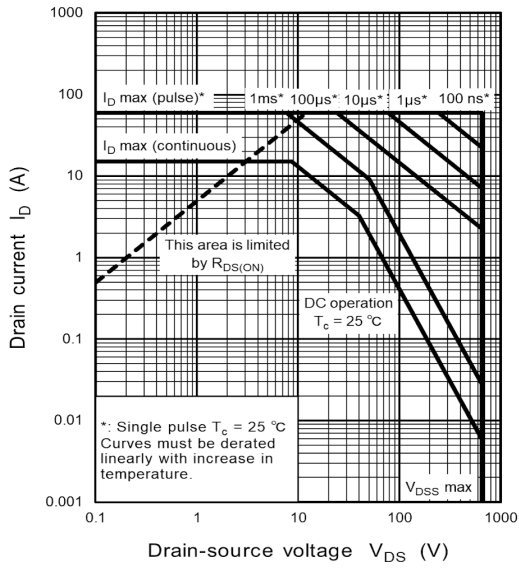


Fig. 8.18 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

Unit: mm



Weight: 0.175 g (typ.)

Package Name(s)
TOSHIBA: 2-8T1A
Nickname: DFN8x8

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